

Title (en)
Sputtering target

Title (de)
Sputtertarget

Title (fr)
Cible de pulvérisation

Publication
EP 1895020 A1 20080305 (EN)

Application
EP 06729897 A 20060324

Priority
• JP 2006305949 W 20060324
• JP 2005182788 A 20050623

Abstract (en)
Provided is a sputtering target having zinc sulfide and indium oxide, zinc oxide and oxide composed of another trivalent positive element A as its primary components, wherein the ratio of sulfur in relation to the total components is 5 to 30wt%, the (111) peak strength I1 of cubic crystal ZnS and the (100) peak strength I2 of hexagonal ZnS measured by XRD coexist, and I1 > I12 is satisfied. The present invention aims to provide a high-strength sputtering target capable of preventing cracks in a target upon manufacturing such a target or when forming a film via sputtering and a manufacturing method of such a sputtering target, as well as a thin film for an optical information recording medium optimal for use as a protective film and a manufacturing method of such a thin film.

IPC 8 full level
C04B 35/453 (2006.01); **C04B 35/547** (2006.01); **C04B 35/626** (2006.01); **C23C 14/34** (2006.01); **G11B 7/24** (2013.01); **G11B 7/254** (2013.01); **G11B 7/257** (2013.01); **G11B 7/2578** (2013.01); **G11B 7/2585** (2013.01); **G11B 7/26** (2006.01)

CPC (source: EP KR US)
C04B 35/453 (2013.01 - EP KR); **C04B 35/547** (2013.01 - EP KR); **C04B 35/62685** (2013.01 - EP); **C23C 14/3414** (2013.01 - EP US); **G11B 7/2548** (2013.01 - KR); **G11B 7/2578** (2013.01 - EP); **G11B 7/26** (2013.01 - KR); **C04B 2235/3217** (2013.01 - EP); **C04B 2235/3225** (2013.01 - EP); **C04B 2235/3227** (2013.01 - EP); **C04B 2235/3284** (2013.01 - EP); **C04B 2235/3286** (2013.01 - EP); **C04B 2235/446** (2013.01 - EP); **C04B 2235/5436** (2013.01 - EP); **C04B 2235/77** (2013.01 - EP); **C04B 2235/785** (2013.01 - EP); **C04B 2235/786** (2013.01 - EP); **C04B 2235/96** (2013.01 - EP); **C04B 2235/9646** (2013.01 - EP); **G11B 7/2585** (2013.01 - EP); **G11B 7/266** (2013.01 - EP); **G11B 2007/25706** (2013.01 - EP); **G11B 2007/25708** (2013.01 - EP); **G11B 2007/25715** (2013.01 - EP); **G11B 2007/25716** (2013.01 - EP); **Y02T 50/60** (2013.01 - US)

Cited by
US8298975B2

Designated contracting state (EPC)
CH LI NL

DOCDB simple family (publication)
EP 1895020 A1 20080305; **EP 1895020 A4 20121114**; CN 101208451 A 20080625; CN 101208451 B 20100616; JP 4907528 B2 20120328; JP WO2006137199 A1 20090108; KR 20080021111 A 20080306; TW 200706665 A 20070216; TW I319438 B 20100111; WO 2006137199 A1 20061228

DOCDB simple family (application)
EP 06729897 A 20060324; CN 200680022785 A 20060324; JP 2006305949 W 20060324; JP 2007522199 A 20060324; KR 20087000003 A 20080102; TW 95113340 A 20060414